

January 2000

FDT434P

P-Channel 2.5V Specified PowerTrench® MOSFET

General Description

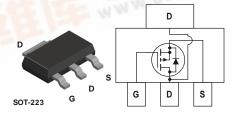
This P-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

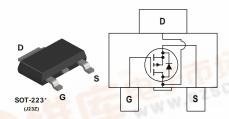
Applications

- Low Dropout Regulator
- DC/DC converter
- Load switch
- Motor driving

Features

- -5.5 A, -20 V. $R_{DS(ON)} = 0.050~\Omega~@~V_{GS} = -4.5~V$ $R_{DS(ON)} = 0.070~\Omega~@~V_{GS} = -2.5~V.$
- Low gate charge (13nC typical)
- High performance trench technology for extremely low R_{DS(ON)}.
- High power and current handling capability in a widely used surface mount package.





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	-6	А
	– Pulsed		-30	
P_D	Power Dissipation for Single Operation	(Note 1a)	3	W
		(Note 1b)	1.3	IV a C
		(Note 1c)	1.1	DZSC
T _J , T _{stg}	Operating and Storage Junction Temperat	ture Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	42	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	12	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
434	FDT434P	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			I	I	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
<u>ΔBVdss</u> ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to $25^{\circ} C$		-28		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate–Body Leakage Current, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage Current, Reverse	$V_{GS} = -8 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.6	-1	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		2		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V}, I_D = -6 \text{ A} $ $V_{GS} = -4.5 \text{ V}, I_D = -6 \text{ A} $ $T_J = 125^{\circ}\text{C}$		0.040 0.067	0.050 0.083	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -4 \text{ A}$ $V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$		0.050	0.070	
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-20			Α
g FS	Forward Transconductance	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -6 \text{ A}$		6.5		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = -10 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		1240		pF
Coss	Output Capacitance	f = 1.0 MHz		270		pF
C _{rss}	Reverse Transfer Capacitance			100		pF
Switchin	ng Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -5 \text{ V}, \qquad I_{D} = -1 \text{ A}, \\ V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		8	16	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		15	25	ns
t _{d(off)}	Turn-Off Delay Time	i		45	65	ns
t _f	Turn-Off Fall Time	7		30	50	ns
$\overline{Q_g}$	Total Gate Charge	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -6 \text{ A},$		13	19	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		1.8		nC
Q _{gd}	Gate-Drain Charge	1		3		nC
Drain-Se	ource Diode Characteristics	and Maximum Ratings		•		
I _s	Maximum Continuous Drain–Source				-1.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -2.1 \text{ A} \text{(Note 2)}$		-0.75	-1.2	V

Notes:

 R_{8JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{8JC} is guaranteed by design while R_{8CA} is determined by the user's board design.



a) 42°C/W when mounted on a 1in² pad of 2 oz copper



b) 95°/W when mounted on a .0066 in² pad of 2 oz copper

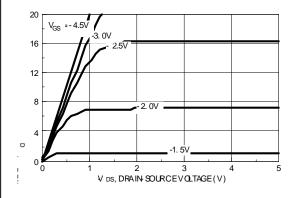


c) 110°/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width $< 300 \mu s$, Duty Cycle < 2.0%

Typical Characteristics



1.8

ON 1.6

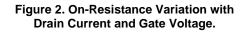
ON 1.6

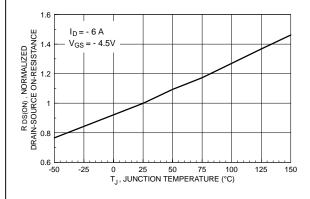
ON 1.6

ON 1.2

O

Figure 1. On-Region Characteristics.





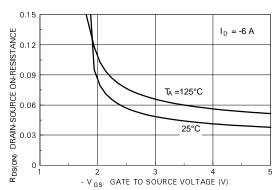
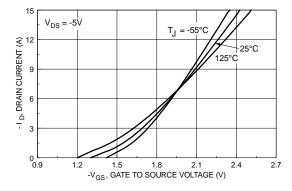


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



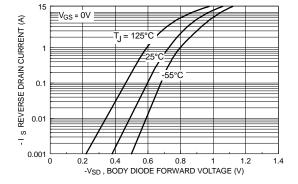
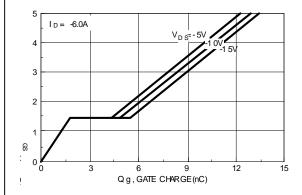


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



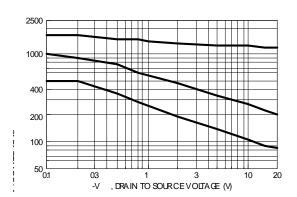


Figure 7. Gate Charge Characteristics.

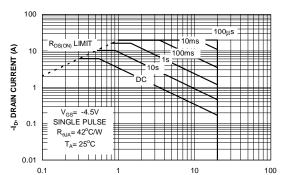


Figure 8. Capacitance Characteristics.

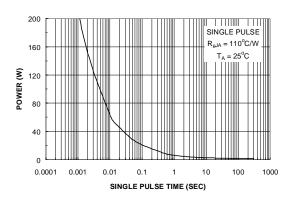


Figure 9. Maximum Safe Operating Area.

-V_{DS} DRAIN-SOURCE VOLTAGE (V)



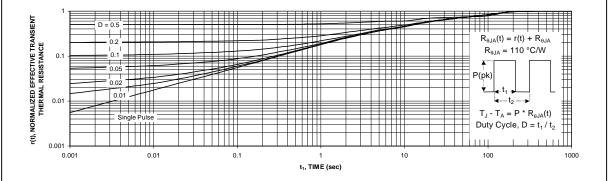
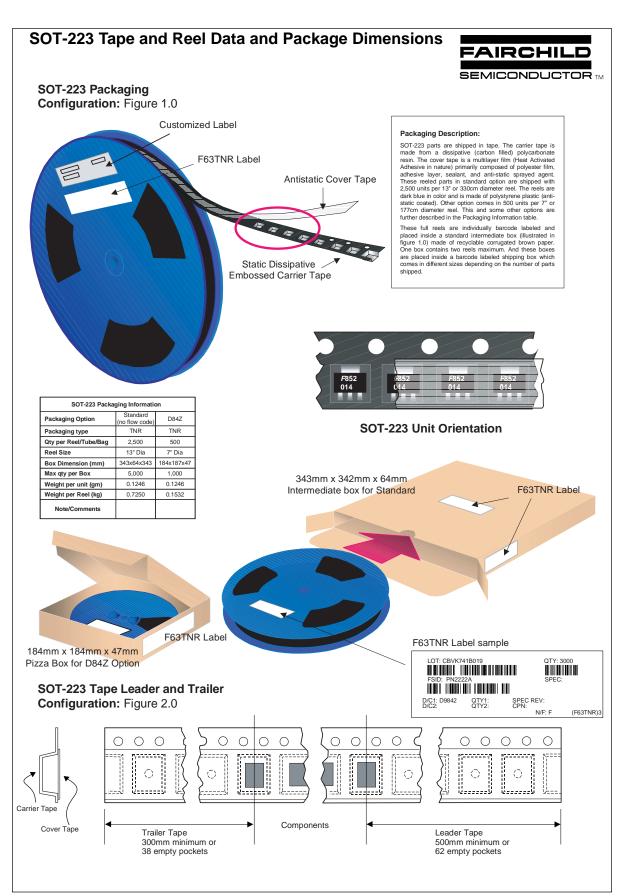


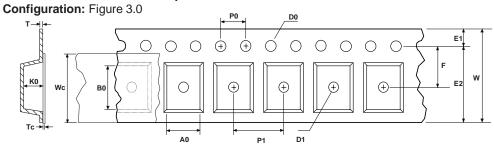
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.



SOT-223 Tape and Reel Data and Package Dimensions, continued

SOT-223 Embossed Carrier Tape



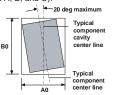
User Direction of Feed	
	$\overline{}$

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-223 (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

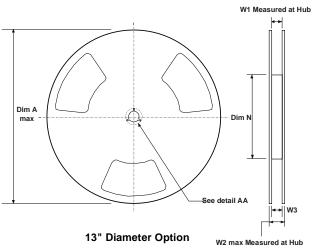


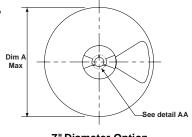
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

SOT-223 Reel Configuration: Figure 4.0



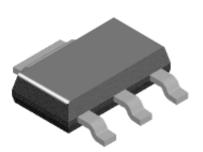


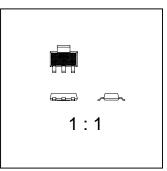
7" Diameter Option B Min Dim D min

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

SOT-223 Tape and Reel Data and Package Dimensions, continued

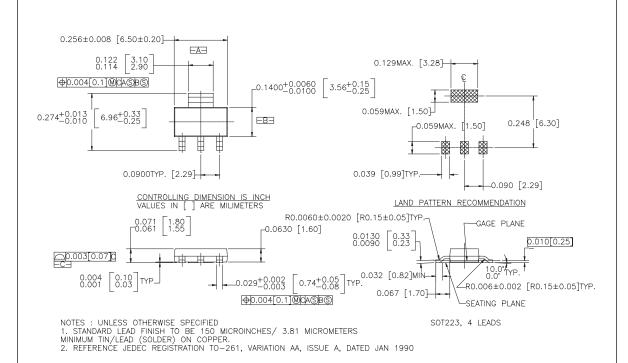
SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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